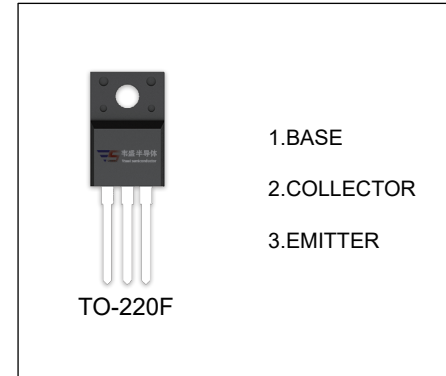


2SB834 TRANSISTOR (PNP)

FEATURES

- Low Collector -emitter saturation voltage
 $V_{CE(sat)}=1.0V(\text{Max})@ I_C=-3A, I_B=-0.3A$
- DC current Gain
 $h_{FE} =60-200@ I_C=0.5A$
- Complementary to NPN 2SD880



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector- Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	1.5	W
$R_{\theta JC}$	Thermal resistance, junction to case	83.3	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-50\text{mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}, I_E=0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-7\text{V}, I_C=0$			-100	μA
DC current gain	$h_{FE(1)*}$	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$	60		200	
	$h_{FE(2)*}$	$V_{CE}=-5\text{V}, I_C=-3\text{A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)*}$	$I_C=-3\text{A}, I_B=-0.3\text{A}$			-1	V
Base-emitter voltage	V_{BE*}	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-500\text{mA}, f=1\text{MHz}$	5			MHz
Turn-on Time	t_{on}	$V_{CC}=-30\text{V}, I_C=-2\text{A}, I_{B1}=I_{B2}=-0.2\text{A}$		0.7		μs
Storage Time	t_{stg}			2.0		μs
Turn-off Time	t_{off}			0.9		μs

*Pulse test.

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	60-120	100-200

Static Characteristic

